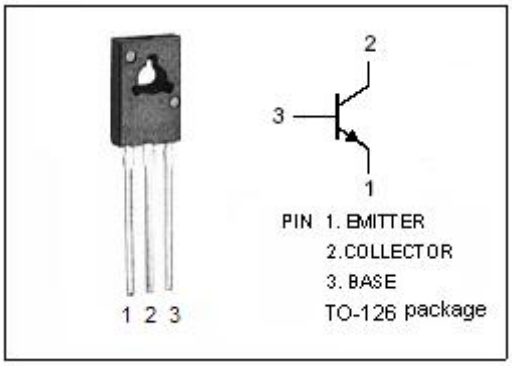
isc Silicon NPN Power Transistor — 2SD1180

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 110V (Min)
- Low collector saturation voltage
- With TO-126 package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

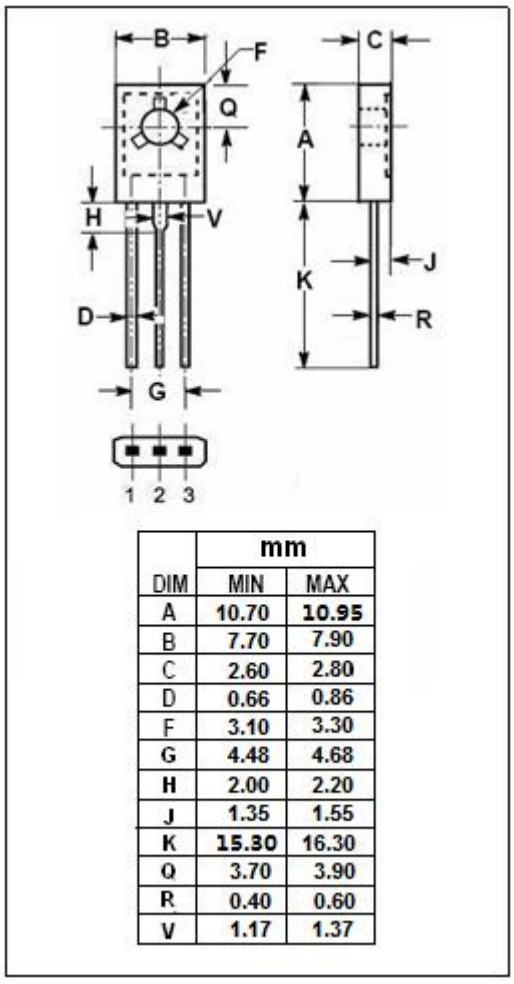


APPLICATIONS

- Designed for use in audio and radio frequency power amplifiers applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	110	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1.5	A
I_{CM}	Collector Current-Peak	2.5	A
P_C	Collector Power Dissipation @ T_a=25℃	1.2	W
	Collector Power Dissipation @ T_C=25℃	20	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; R_{BE}= ∞	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=100μA; I_E=0	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 0.1mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			0.7	V
$V_{BE(sat))}$	Base-emitter saturation voltage	I_C= 1A; I_B= 0.2A			1.3	V
I_{CBO}	Collector Cutoff Current	V_{CE}= 120V; I_E= 0			1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=3V; I_C=0			1	μA
h_{FE}	DC Current Gain	I_C=150mA; V_{CE}= 5V	100			